



2SB921L/2SD1237L

80V/7A Switching Applications

Applications

- Suitable for relay drivers, high-speed inverters, converters, and other general large current switching applications.

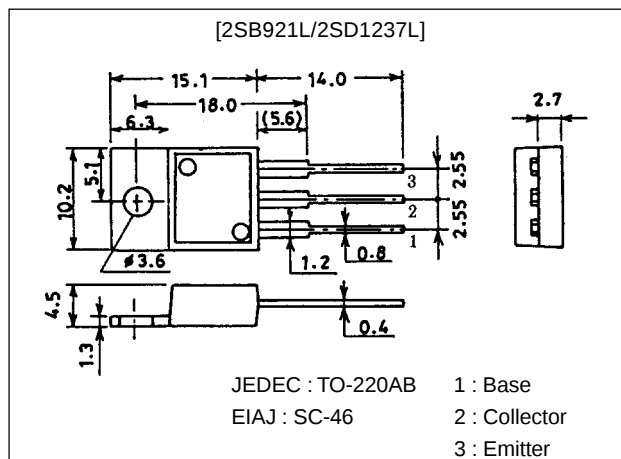
Features

- Low collector-to-emitter saturation voltage : $V_{CE(sat)} = -0.5V$ (PNP), $0.4V$ (NPN) max.
- Large current capacity.

Package Dimensions

unit:mm

2010C



() : 2SB921L

Specifications

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(-)90	V
Collector-to-Emitter Voltage	V_{CEO}		(-)80	V
Emitter-to-Base Voltage	V_{EBO}		(-)6	V
Collector Current	I_C		(-)7	A
Collector Current (Pulse)	I_{CP}		(-)12	A
Collector Dissipation	P_C		1.75	W
		$T_c = 25^\circ\text{C}$	40	W
Junction Temperature	T_j		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)80V, I_E = 0$			(-)0.1	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$			(-)0.1	mA
DC Current Gain	h_{FE1}	$V_{CE} = (-)2V, I_C = (-)1A$	70*		280*	
	h_{FE2}	$V_{CE} = (-)2V, I_C = (-)4A$	30			
Gain-Bandwidth Product	f_T	$V_{CE} = (-)5V, I_C = (-)1A$		20		MHz
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)4A, I_B = (-)0.4A$			0.4	V
					(-0.5)	V

* : The 2SB921/2SD1237 are graded as follows by h_{FE} at 1A :

70	Q	140	100	R	200	140	S	280
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SANYO Electric Co., Ltd. Semiconductor Business Headquarters

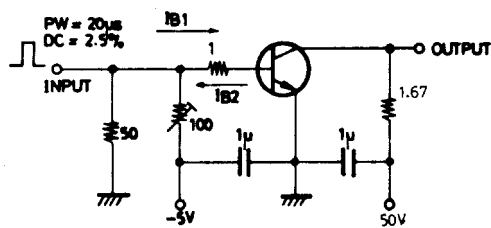
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

92098HA (KT)/D251MH/4077KI/N275MW No.1797-1/4

2SB921L/2SD1237L

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)1mA, I_E = 0$	(-)90			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)80			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)1mA, I_C = 0$	(-)6			V
Turn-ON Time	t_{on}	See specified Test Circuit		(0.2)		μs
				0.1		μs
Storage Time	t_{stg}	See specified Test Circuit		(0.7)		μs
				1.6		μs
Fall Time	t_f	See specified Test Circuit		(0.2)		μs
				0.4		μs

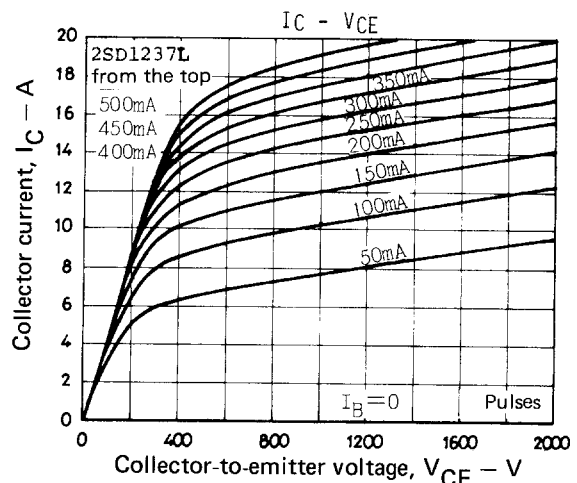
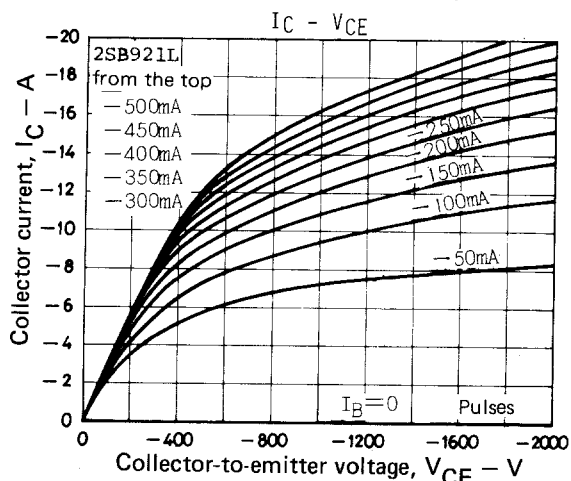
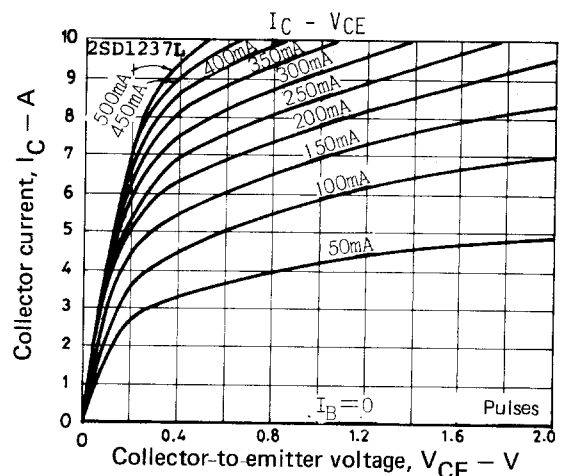
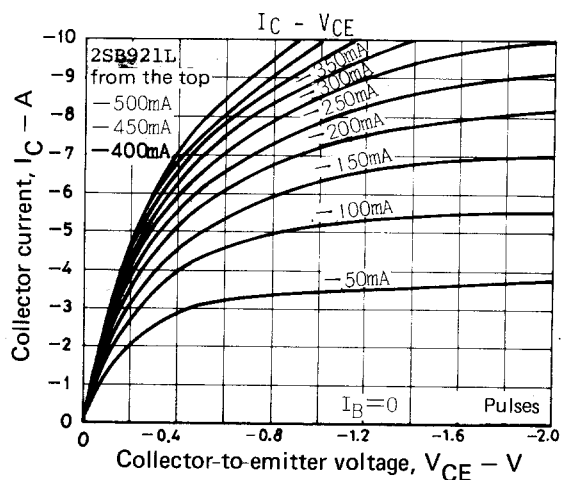
Switching Time Test Circuit



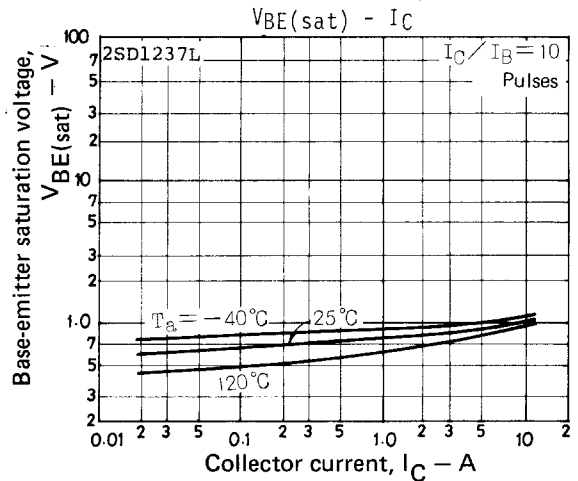
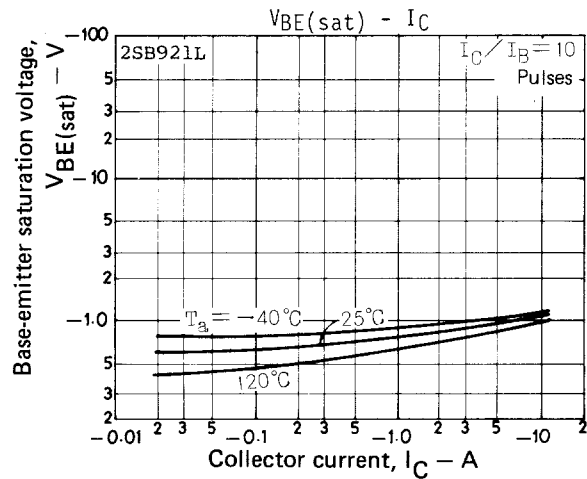
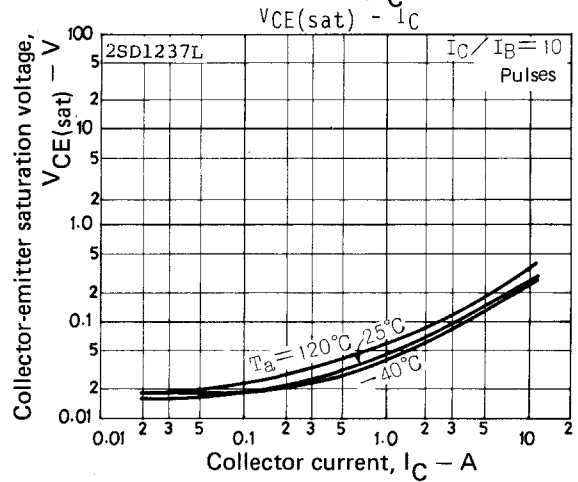
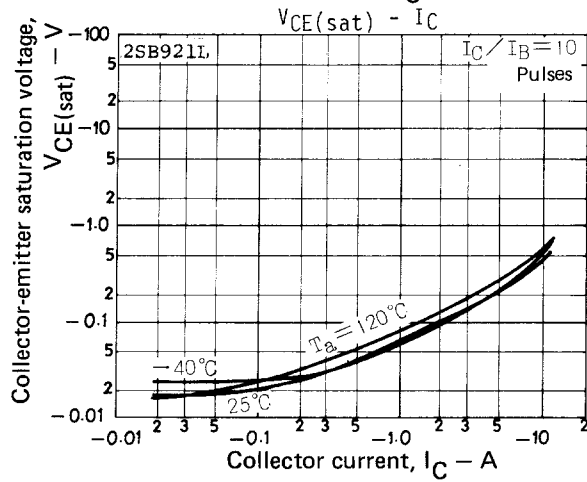
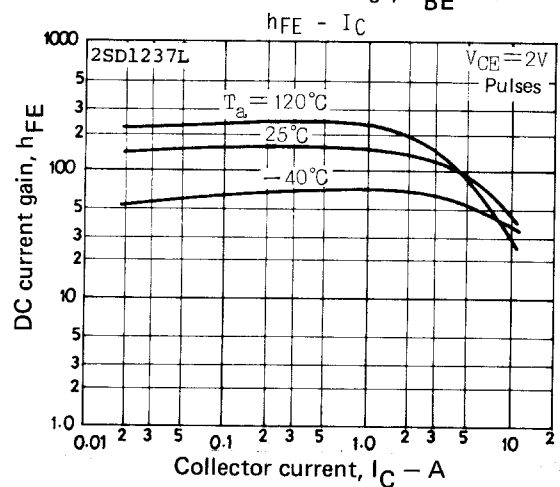
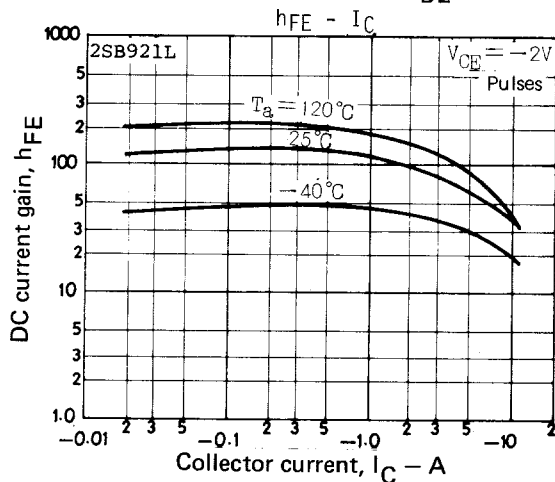
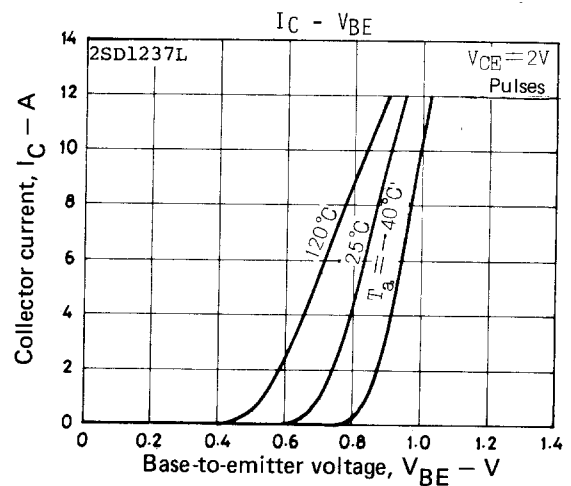
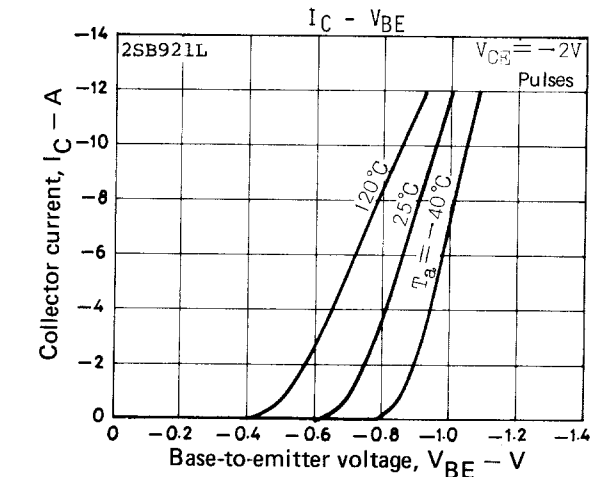
(For PNP, the polarity is reversed)

$$10I_{B1} = -10I_{B2} = I_C = 2A$$

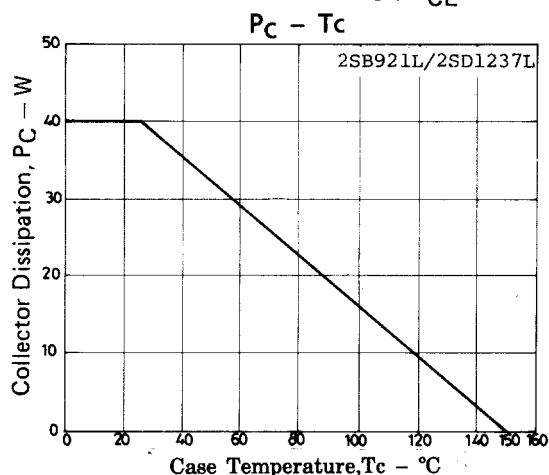
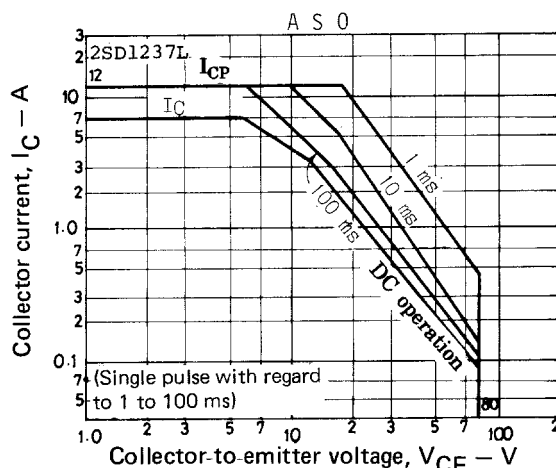
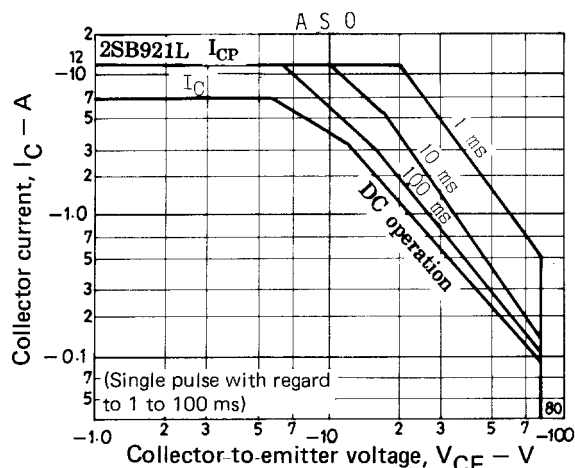
Unit (resistance : Ω , capacitance : F)



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